

N-Channel 60 V (D-S) Super Junction MOSFET

PRODUCT SUMMARY							
V _{DS} (V)	$R_{DS(on)}$ (m Ω)(Typ.)	I _D (A) ^a	Q _g (Typ.)				
60	0.86 at V _{GS} = 10 V	330	109 nC				

FEATURES

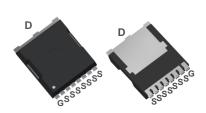
- DT- SJ Power MOSFET
- $\bullet\,$ 100 % $\rm R_{\rm g}$ and UIS Tested
- Low RDS(ON)

RoHS

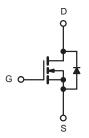
APPLICATIONS

- DC/DC Converter
- Ideal for high-frequency switching and synchronous rectification

TOLL Pin Configuration



Top View



N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS (T _C = 25 °C, unless otherwise noted)							
PARAMETER	SYMBOL	LIMIT	UNIT				
Drain-Source Voltage	V _{DS}	60	V				
Gate-Source Voltage	V _{GS}	± 20					
Continuous Drain Current (T _J = 175 °C) ^a	T _C = 25 °C		330				
Continuous Diam Current (1) = 175 C)	T _C = 100 °C	- I _D	250	Α			
Pulsed Drain Current ^b	I _{DM}	1320					
Single Avalanche Energy	E _{AS}	2010	mJ				
Maximum Power Dissipation ^c	T _C = 25 °C	В	326	W			
Maximum Fower Dissipation	T _C = 100 °C	- P _D	163] VV			
Operating Junction and Storage Temperature R	T _J , T _{stg}	- 55 to + 175	°C				

THERMAL RESISTANCE RATINGS							
PARAMETER		LIMIT	UNIT				
Junction-to-Ambient (PCB Mount) ^d	R _{thJA}	40	°C/W				
Junction-to-Case (Drain)	R _{thJC}	0.46	- 'C/VV				

Notes

- a. Calculated continuous current based on maximum allowablejunction temperature.
- b. Repetitive rating; pulse width limited by max. junction temperature.
- c. $\,$ Pd is based on max. junction temperature, using junction-case thermal resistance.
- d. The value of R_{8JA} is measured with the device mounted on 1 in 2 FR-4 board with 2oz. Copper,in a still air environment with Ta=25 °C.



SPECIFICATIONS (T _C = 25 °C, unless otherwise noted)									
PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT				
Static									
Drain-Source Breakdown Voltage	V _{DS}	V _{GS} = 0 V, I _D = 250 μA	60	-	-	V			
Gate Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250 μA	2	-	4	V			
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$	-	-	± 100	nA			
Zero Gate Voltage Drain Current	1	$V_{DS} = 60 V, V_{GS} = 0 V$	-	-	1	μA			
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 48 V, V _{GS} = 0 V, T _J = 125 °C	-	-	100				
On-State Drain Current ^a	I _{D(on)}	V _{DS} ≥ 5 V, V _{GS} = 10 V	330	-	-	Α			
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = 10 V, I _D = 20 A	-	0.86	1.1	mΩ			
Forward Transconductance ^a	9fs	V _{DS} = 5 V, I _D = 20 A	-	76	-	S			
Dynamic ^b									
Input Capacitance	C _{iss}		-	7208	-	pF			
Output Capacitance	C _{oss}	$V_{GS} = 0 \text{ V}, V_{DS} = 30 \text{ V}, f = 1 \text{ MHz}$	-	3130	-				
Reverse Transfer Capacitance	C _{rss}		-	205	-				
Total Gate Charge ^c	Qg		-	109	-	nC			
Gate-Source Charge ^c	Q_{gs}	$V_{DS} = 30 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 20 \text{ A}$	-	27	-				
Gate-Drain Charge ^c	Q_{gd}		-	25	-				
Gate Resistance	R_g	f = 1 MHz	-	2.4	-	Ω			
Turn-On Delay Time ^c	t _{d(on)}		-	25	-				
Rise Time ^c	t _r	$V_{DD} = 30 \text{ V}, I_D = 20 \text{ A}, R_g = 3 \Omega$	-	35	-	ns			
Turn-Off Delay Time ^c	t _{d(off)}	V _{GS} = 10 V	-	64	-				
Fall Time ^c	t _f		-	88	-				
Drain-Source Body Diode Ratings and	Characterist	ics ^b (T _C = 25 °C)							
Continuous Source-Drain Diode Current I _S		T _C = 25 °C	-	-	330	Α			
Pulsed Current	I _{SM}		-	-	1320	Α			
Forward Voltage ^a	V _{SD}	I _F = 1A, V _{GS} = 0 V	-	0.7	1.2	V			
Reverse Recovery Time	t _{rr}	I _F = 20 A, di/dt = 100 A/μs	-	73	-	ns			
Reverse Recovery Charge	Q _{rr}			110	-	nC			

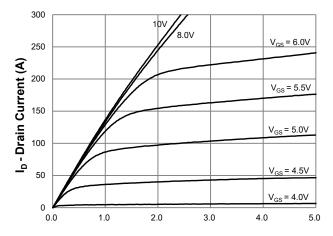
Notes

- a. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %.
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those in dicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended pe riods may affect device reliability.

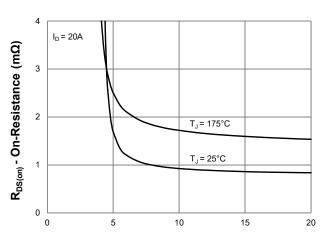


TYPICAL CHARAC TERISTICS (25 °C, unless otherwise noted)



V_{DS} - Drain-to-Source Voltage (V)

Figure 1: Output Characteristics



V_{GS} - Gate-to-Source Voltage (V)

Figure 3: On-Resistance vs. Gate-Source Voltage

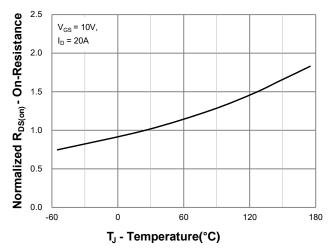
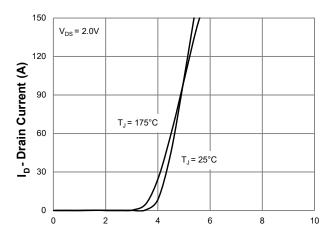


Figure 5: On-Resistance vs. Junction Temperature



V_{GS}- Gate-to-Source Voltage (V)

Figure 2: Transfer Characteristics

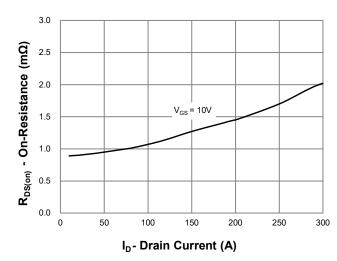
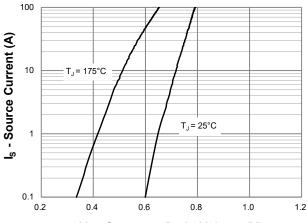


Figure 4: On-Resistance vs. Gate-Source Voltage

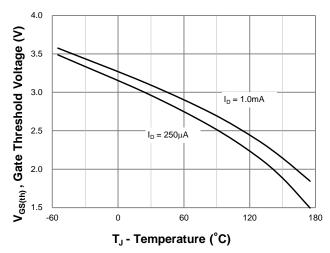


V_{SD}-Source-to-Drain Voltage (V)

Figure 6: Source-Drain Diode Forward Voltage



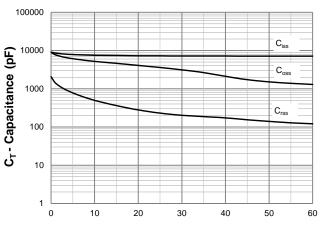
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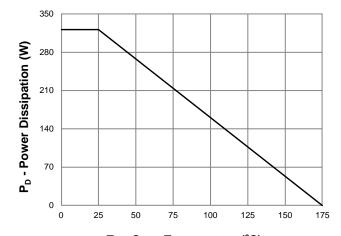
Figure 7: Gate Threshold Variation vs. Junction Temperature

Q_g - Total Gate Charge (nC)
Figure8: Gate Charge Characteristics

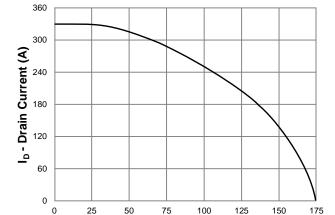


V_{DS} - Drain-to-Source Voltage (V)

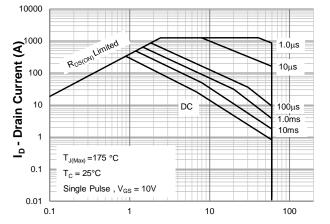
Figure 9: Capacitance Characteristics



T_C - Case Temperature (°C) Figure 10: Power Derating



T_C - Case Temperature (°C) Figure 11: Current Derating



 $\mbox{V}_{\mbox{\scriptsize DS}}$ - Drain-to-Source Voltage (V)

Figure 12: Safe Operating Area



TYPICAL CHARAC TERISTICS (25 °C, unless otherwise noted)

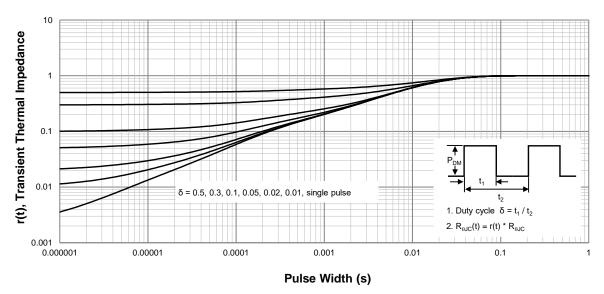
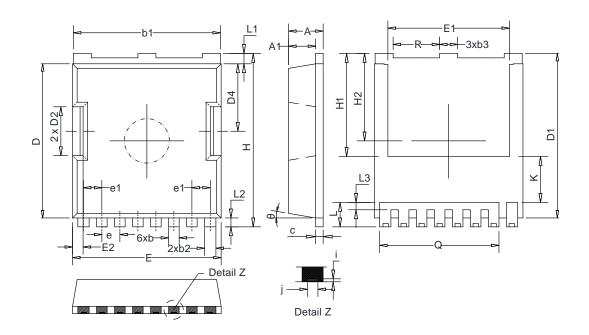


Figure 13: Normalized Maximum Transient Thermal Impedance



TOLL PACKAGE OUTLINE



COMMON DIMENSIONS (UNITS OF MEASURE=MILLIMETER)

Symbol	Min	Тур	Max	Symbol	Min	Тур	Max	
А	2.05	2.30	2.65	E2	0.40	0.70	0.90	
A1	1.50	1.80	2.10	Н	11.30	11.70	12.10	
b	0.50	0.70	0.90	H1	6.95 BSC			
b1	9.50	9.80	10.05	H2	5.90 BSC			
b2	0.50	0.75	1.00	i	0.10 REF			
b3	1.00	1.20	1.45	j	0.35 REF			
С	0.30	0.50	0.75	K	3.10 REF			
D	10.10	10.40	10.70	L	1.45	1.65	1.85	
D1	10.80	11.10	11.40	L1	0.50	0.70	0.90	
D2	3.10	3.30	3.50	L2	0.40	0.60	0.80	
D4	4.35	4.55	4.80	L3	0.30	0.50	0.70	
е	1.20 BSC			Q	7.95 REF			
e1	1.225 BSC			R	2.80	3.10	3.35	
Е	9.65	9.90	10.15	θ	10°REF			
E1	7.80	8.10	8.50					





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